Analog Power AM2305P

P-Channel 20-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low r_{DS(on)} and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

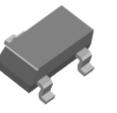
•	Low $r_{DS(on)}$ provides higher efficiency and
	extends battery life

- Low thermal impedance copper leadframe SOT-23 saves board space
- Fast switching speed
- High performance trench technology



 $V_{DS}(V)$

-20



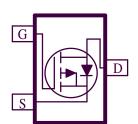
PRODUCT SUMMARY

 $\underline{\eta_{DS(on)}}$ (OHM)

 $0.043 @ V_{CS} = -4.5V$

 $0.054 @ V_{CS} = -2.5V$

 $0.120 @ V_{CS} = -1.8V$



 $\mathbf{I}_{\mathbf{D}}(\mathbf{A})$

-4.5

-4.0

-2.7

RoHS
COMPLIAN
HALOGE
FREE

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Ratings	Units	
Drain-Source Voltage —			-20	* 7	
Gate-Source Voltage			±8	V	
Continue Durin Connect ^a	$T_A=25^{\circ}C$	T	-4.5	A	
Continuous Drain Current ^a	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	¹ D	-3.6		
Pulsed Drain Current ^b		I_{DM}	-10		
Decree Disciplination a	$T_A=25^{\circ}C$	P_{D}	1.25	W	
Power Dissipation ^a	$\begin{array}{c} T_{A}=25^{\circ}C \\ \hline T_{A}=70^{\circ}C \end{array} P_{D}$		0.8	**	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maniana Innation to Ambient ^a	t <= 5 sec	D	100	0C/M	
Maximum Junction-to-Ambient ^a	Steady-State	K_{THJA}	150	°C/W	

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature b.

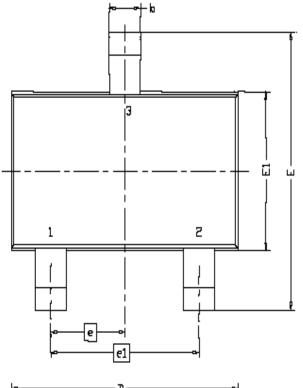
SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)						
Parameter		Test Conditions	Limits			Unit
rarameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static						
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250 \text{ uA}$	-0.7			
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			±100	nA
Zero Gate Voltage Drain Current	$I_{ m DSS}$	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1	uA
Zero Gate Voltage Drain Current	¹ DSS	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-10	
On-State Drain Current ^A	$I_{D(on)}$	$V_{DS} = -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-10			A
	r _{DS(on)}	$V_{GS} = -4.5 \text{ V}, I_D = -3.6 \text{ A}$			43	
Drain-Source On-Resistance ^A		$V_{GS} = -2.5 \text{ V}, I_D = -3.1 \text{ A}$			54	mΩ
		$V_{GS} = -1.8 \text{ V}, I_D = -2.7 \text{ A}$			120	
Forward Tranconductance ^A	${f g}_{ m fs}$	$V_{DS} = -5 \text{ V}, I_D = -1.25 \text{ A}$		12		S
Diode Forward Voltage	V_{SD}	$I_S = -0.46 \text{ A}, V_{GS} = 0 \text{ V}$		-0.60		V
Dynamic ^b						
Total Gate Charge	Q_{g}	$V_{DS} = -5 \text{ V}, V_{GS} = -4.5 \text{ V},$		12.0		
Gate-Source Charge	Q_{gs}	$I_{DS} = -3 \text{ V}, V_{GS} = -4.3 \text{ V},$ $I_{D} = -2.4 \text{ A}$		2.0		nC
Gate-Drain Charge	Q_{gd}			2.0		
Turn-On Delay Time	$t_{d(on)}$			6.5		
Rise Time	t _r	$V_{DD} = -10 \text{ V}, I_{L} = -1 \text{ A},$ $V_{GEN} = -4.5 \text{ V}, R_{G} = 6 \Omega$		20		ns
Turn-Off Delay Time	$t_{d(off)}$			31		
Fall-Time	$t_{ m f}$			21		

Notes

- a. Pulse test: $PW \le 300$ us duty cycle $\le 2\%$.
- b. Guaranteed by design, not subject to production testing.

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Package Information



DIM.	MILLIMETERS				
יויות	MIN	NDM	MAX		
Α	0.935	0.95	1.10		
A1	0.01		0.10		
A2	0.85	0.90	0.925		
Ь	0.30	0.40	0.50		
С	0.10	0.15	0,25		
D	2.70	2.90	3.10		
Ε	2.60	2.80	3.00		
E1	1 1.40 1.6		1.80		
6	0.95 BSC				
el	1.90 BSC				
L	0.30	0.40	0.60		
L1	0.60REF				
L2	0.25BSC				
R	0.10				
θ	Û.	4*	8,		
81	7*N□M				

